



A Product Line of Diodes Incorporated



DXT2013P5

100V PNP MEDIUM POWER TRANSISTOR Power $\text{DI}^{\$}5$

Features

- 43% smaller than SOT223; 60% smaller than TO252
- Maximum height just 1.1mm
- Rated up to 3.2W
- V_{CEO} = -100V
- I_C = -5A; I_{CM} = -10A
- Low Saturation voltage
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Applications

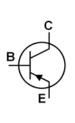
SLIC DC-DC Converter

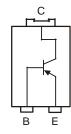
Mechanical Data

- Case: PowerDI[®]5
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.093 grams (approximate)









Top View

Bottom View

Device Schematic

Pin-out diagram

Ordering Information (Note 3)

Part Number	Case	Packaging	
DXT2013P5-13	PowerDI [®] 5	5000/Tape & Reel	

1. No purposefully added lead. Halogen and Antimony Free.

2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

3. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

Notes:



DXT2013 = Product Type Marking Code DII = Manufacturers' Code Marking K = Factory Designator YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 09 for 2009) WW = Week code (01 to 53)





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-140	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ι _C	-5	A
Peak Pulse Current	I _{CM}	-10	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
	Symbol	value	Onit
Power Dissipation @ $T_A = 25^{\circ}C$ (Note 4)	PD	3.2	W
Thermal Resistance, Junction to Ambient Air (Note 4) $@T_A = 25^{\circ}C$	$R_{ ext{ heta}JA}$	39	°C/W
Power Dissipation @ $T_A = 25^{\circ}C$ (Note 5)	PD	1.7	W
Thermal Resistance, Junction to Ambient Air (Note 5) $@T_A = 25^{\circ}C$	$R_{ ext{ heta}JA}$	75	°C/W
Power Dissipation @ $T_A = 25^{\circ}C$ (Note 6)	PD	0.74	W
Thermal Resistance, Junction to Ambient Air (Note 6) $@T_A = 25^{\circ}C$	$R_{ ext{ heta}JA}$	169	°C/W
Thermal Resistance, Junction to Collector Terminal	R _θ JT	5.6	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

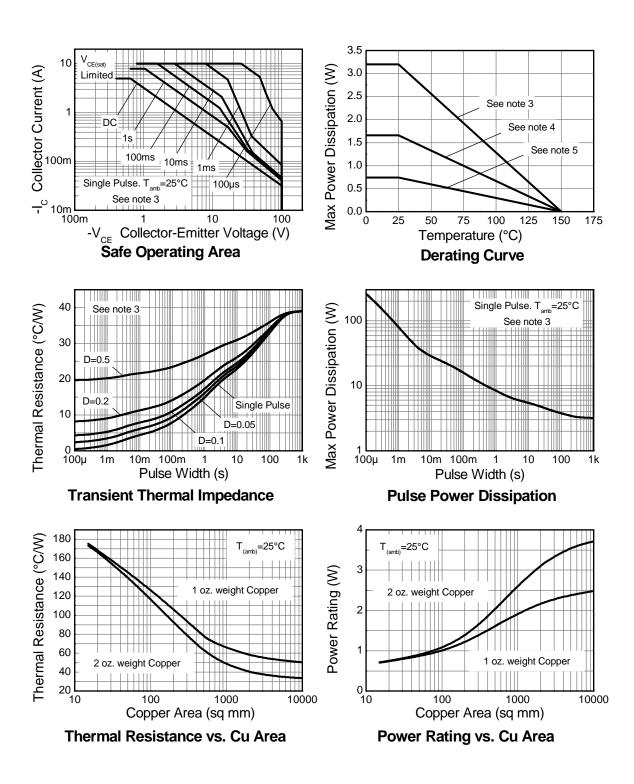
 Device mounted on FR-4 PCB, single sided 2 oz. copper, collector pad dimensions 50mm x 50mm.
 Device mounted on FR-4 PCB, single sided 1 oz. copper, collector pad dimensions 25mm x 25mm.
 Device mounted on FR-4 PCB, single sided 1 oz. copper, minimum recommended pad layout. Notes:



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Electrical Characteristics @T_A = 25°C unless otherwise specified

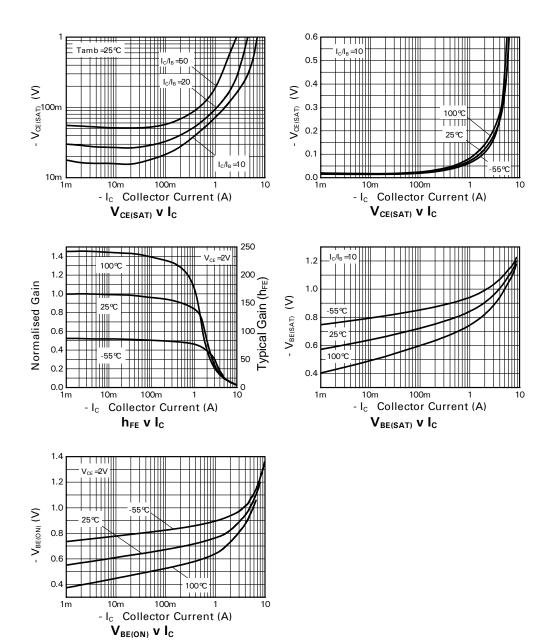
			_			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-140	-160	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 7)	V _{(BR)CEO}	-100	-115	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-7.0	-8.1	_	V	$I_E = -100 \mu A$
Collector Cutoff Current	I _{CBO}	_	<1 —	-20 -0.5	nA μA	V _{CB} = -100V V _{CB} = -100V, T _{amb} = 100 °C
Collector Cutoff Current	I _{CER} R≤1kΩ	_	<1 —	-20 -0.5	nA μA	V _{CB} = -100V V _{CB} = -100V, T _{amb} = 100 °C
Emitter Cutoff Current	I _{EBO}	_	<1	-10	nA	V _{EB} = -6V
Collector-Emitter Saturation Voltage (Note 7)	V _{CE(sat)}	_	-20 -70 -120 -240	-30 -90 -150 -340	mV	I _C = -0.1A, I _B = -10mA I _C = -1A, I _B = -10mA I _C = -2A, I _B = -200mA I _C = -4A, I _B = -400mA
Base-Emitter Saturation Voltage (Note 7)	V _{BE(sat)}	_	-985	-1100	mV	I _C = -4A, I _B = -400mA
Base-Emitter Turn-On Voltage (Note 7)	V _{BE(on)}		-920	-1050	mV	$V_{CE} = -4V, I_{C} = -2A$
DC Current Gain (Note 7)	h _{FE}	100 100 25 15 —	250 200 50 30 5	 300 	_	$\begin{split} I_{C} &= -10 \text{mA}, \ V_{CE} &= -1 \text{V} \\ I_{C} &= -1 \text{A}, \ V_{CE} &= -1 \text{V} \\ I_{C} &= -3 \text{A}, \ V_{CE} &= -1 \text{V} \\ I_{C} &= -4 \text{A}, \ V_{CE} &= -1 \text{V} \\ I_{C} &= -10 \text{A}, \ V_{CE} &= -1 \text{V} \end{split}$
Transition Frequency	f _T		125	_	MHz	$I_{C} = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 50MHz
Output Capacitance	C _{obo}		42	_	pF	V _{CB} = -10V, f = 1MHz
Switching Times	t _{on} t _{off}		42 540		ns ns	$I_{C} = -1A, V_{CC} = -10V,$ $I_{B1} = I_{B2} = -100mA$

Notes: 7. Pulse Test: Pulse width ≤300µs. Duty cycle ≤2.0%.





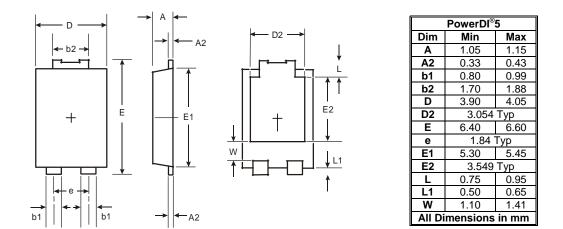
Typical Characteristic



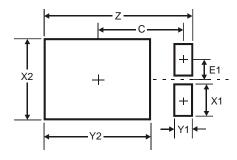




Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
Z	6.6
X1	1.4
X2	3.6
Y1	0.8
Y2	4.7
С	3.87
E1	0.9





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